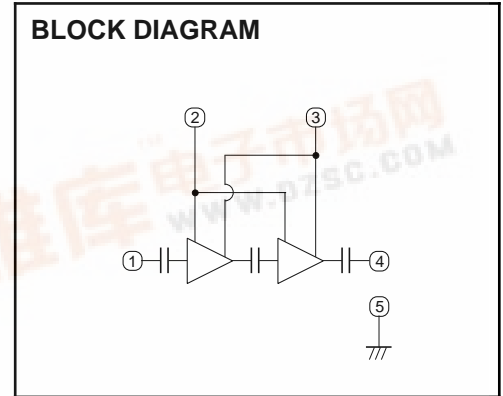
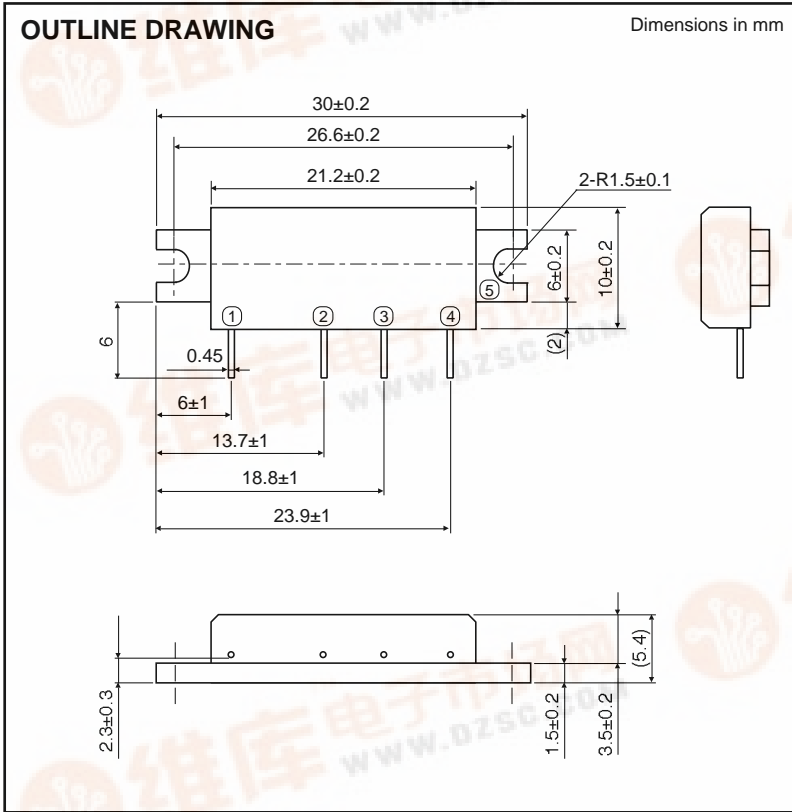


MITSUBISHI RF POWER MODULE

M68739M

SILICON MOS FET POWER AMPLIFIER, 155-168MHz, 7W, FM PORTABLE RADIO



PIN:

- ①Pin : RF INPUT
- ②VGG : GATE BIAS SUPPLY
- ③VDD : DRAIN BIAS SUPPLY
- ④Po : RF OUTPUT
- ⑤GND: FIN

**ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	VGG 2.5V, ZG=ZL=50	16	V
VGG	Gate bias voltage		3	V
Pin	Input power	f=155-168MHz, ZG=ZL=50	30	mW
Po	Output power	f=155-168MHz, ZG=ZL=50	10	W
Tc (OP)	Operation case temperature	f=155-168MHz, ZG=ZL=50	-30 to +100	°C
Tstg	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

**ELECTRICAL CHARACTERISTICS** (Tc=25°C, ZG=ZL=50 unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		155	168	MHz
Po	Output power	VDD=9.6V, VGG=2.5V, Pin=20mW	7		W
η	Total efficiency		50		%
2fo	2nd. harmonic			-20	
in	Input VSWR			4	-
-	Stability	ZG=50, VDD=4.8-13.2V, Load VSWR <4:1	No parasitic oscillation		-
-	Load VSWR tolerance	VDD=13.2V, Pin=20mW, PO=7W (VGG Adjust), ZL=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

